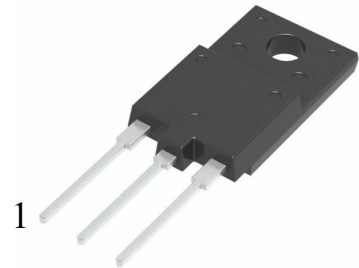


◆ Features:

- ✧ Fast switching speed
开关速度快
- ✧ High input impedance and low level drive
高输入阻抗和低电平驱动
- ✧ Avalanche energy tested
雪崩能量测试
- ✧ Improved dv/dt capability, high ruggedness
提高 dv/dt 能力, 高耐用性

◆ Applications

- ✧ High efficiency switch mode power supplies
高效率开关电源
- ✧ Power factor correction
功率因数校正
- ✧ Electronic lamp ballast
电子整流器


TO-3PF


TO-3PF		mm		
SYMBOL		MIN	NOM	MAX
A		15.30	15.50	15.70
B		4.30	4.50	4.70
C		21.80	22.00	22.20
D		38.70	39.00	39.30
E		5.45BSC		
F		5.45BSC		
G		1.80	2.00	2.20
H		3.80	4.00	4.20
I		0.75	0.85	0.95
K		3.45	3.60	3.75
L		2.80	3.00	3.20
M		5.30	5.50	5.70
N		22.8	23.00	23.2
O		3.25	3.40	3.55
P		0.80	0.90	1.00

◆ Absolute Maximum Ratings (Tc=25°C)

Symbol	Parameters	Ratings	Unit
V _{DSS}	Drain-Source Voltage 漏源电压	1500	V
V _{GS}	Gate-Source Voltage-Continuous 栅源电压	±30	V
I _D	Drain Current-Continuous (Note 2) 漏极持续电流	3	A
I _{DM}	Drain Current-Single Plused (Note 1) 漏极单次脉冲电流	12	A
P _D	Power Dissipation (Note 2) 功率损耗	400	W
T _j	Max.Operating junction temperature 最大结温	150	°C

◆ Electrical characteristics (Tc=25°C unless otherwise noted)

Symbo l	Parameters	Min	Typ	Max	Units	Conditions
Static Characteristics						
B _{VDSS}	Drain-Source Breakdown VoltageCurrent (Note 1) 漏极击穿电压	1500	--	--	V	I _D =250μA, V _{GS} =0V, T _J =25°C
V _{GS(th)}	Gate Threshold Voltage 栅极开启电压	3.0	--	5.0	V	V _{DS} =V _{GS} , I _D =250μA
R _{DS(on)}	Drain-Source On-Resistance 漏源导通电阻	--	6.3	--	Ω	V _{GS} =10V, I _D =1.5A
I _{GSS}	Gate-Body Leakage Current 栅极漏电流	--	--	±100	nA	V _{GS} =±30V, V _{DS} =0
I _{DSS}	Zero Gate Voltage Drain Current 零栅极电压漏极电流	--	--	10	μA	V _{DS} =1500V, V _{GS} =0
g _{fs}	Forward Transconductance 正向跨导	--	5.8	--	S	V _{DS} =30V, I _D =3A

**OSHF3N150****1500V N-CHANNEL MOSFET**

Switching Characteristics						
T _{d (on)}	Turn-On Delay Time 开启延迟时间	--	30	--	ns	V _{DS} =750V, I _D =3A, R _G =4.7Ω (Note 2)
T _r	Rise Time 上升时间	--	55	--	ns	
T _{d (off)}	Turn-Off Delay Time 关闭延迟时间	--	105	--	ns	
T _f	Fall Time 下降时间	--	115	--	ns	
Q _g	Total Gate Charge 栅极总电荷	--	37	--	nC	V _{DS} =600V , V _{GS} =10V, I _D =4A (Note 2)
Q _{gs}	Gate-Source Charge 栅源极电荷	--	6	--	nC	
Q _{gd}	Gate-Drain Charge 栅漏极电荷	--	22	--	nC	
Dynamic Characteristics						
C _{iss}	Input Capacitance 输入电容	--	825	--	pF	V _{DS} =25V, V _{GS} =0, f=1MHz
C _{oss}	Output Capacitance 输出电容	--	125	--	pF	
C _{rss}	Reverse Transfer Capacitance 反向传输电容	--	30	--	pF	
I _S	Continuous Drain-Source Diode Forward Current (Note 2) 二极管导通正向持续电流	--	--	3	A	
V _{SD}	Diode Forward On-Voltage 二极管正向导通电压	--	--	1.6	V	I _S =3A, V _{GS} =0
R _{th(j-c)}	Thermal Resistance, Junction to Case 结到外壳的热阻	--	--	0.31	°C/W	

Note 1: Repetitive Rating : Pulse width limited by maximum junction temperature

Note 2: Pulse test: PW ≤ 300us , duty cycle ≤ 2%.